

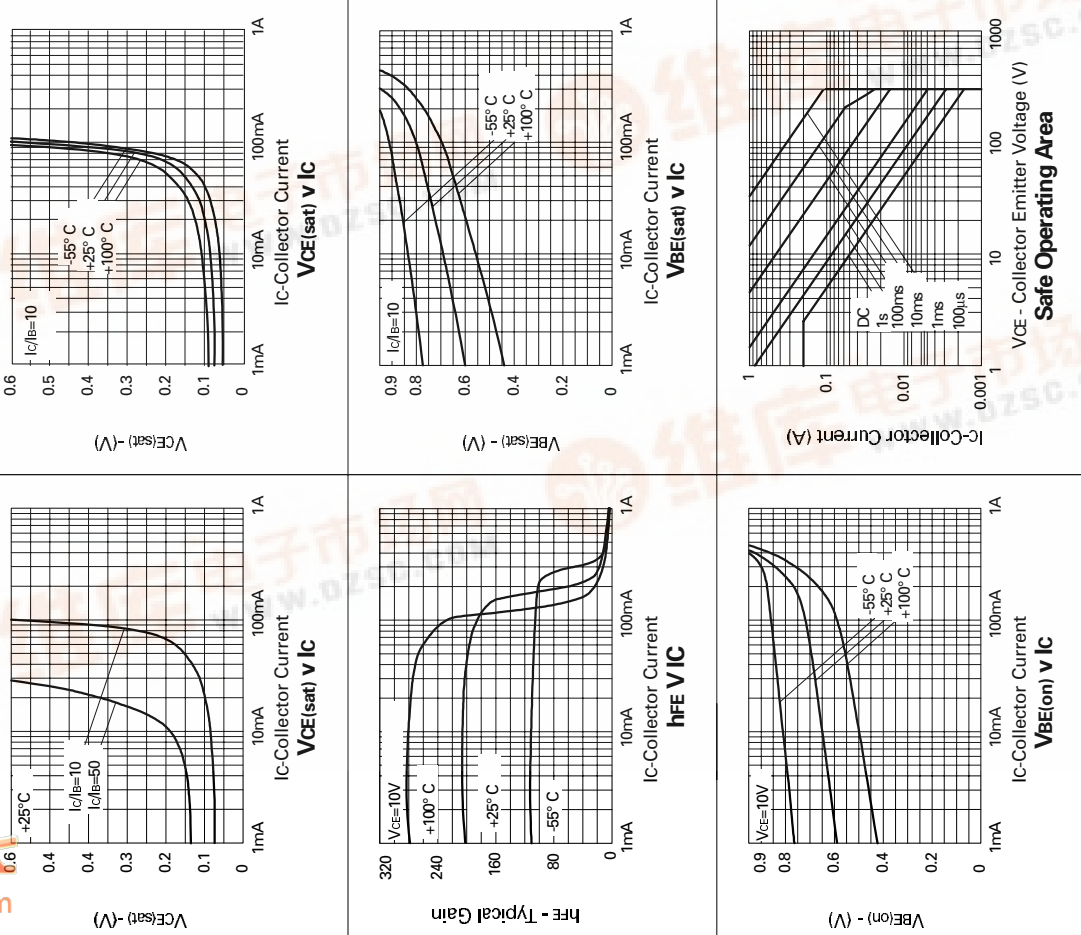
# SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

ISSUE 3 - OCTOBER 1995

# FM597

COMPLEMENTARY TYPE FM597  
PARTMARKING DETAIL - 597

## TYPICAL CHARACTERISTICS



## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CB0}$	-300	V
Collector-Emitter Voltage	$V_{CE0}$	-300	V
Emitter-Base Voltage	$V_{EB0}$	-5	V
Peak Pulse Current	$I_{CM}$	-1	A
Continuous Collector Current	$I_C$	-0.2	A
Base Current	$I_B$	-200	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	$P_{tot}$	500	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150	$^\circ\text{C}$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ ).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$		-100	nA	$V_{CB} = -250\text{V}$
Emitter Cut-Off Current	$I_{EBO}$		-100	nA	$V_{EB} = -4\text{V}$
Collector-Emitter Cut-Off Current	$I_{CES}$		-100	nA	$V_{CES} = -250\text{V}$
Emitter Saturation Voltages	$V_{CE(sat)}$	-0.25	-0.25	V	$I_C = -50\text{mA}, I_B = -5\text{mA}$ $I_C = -100\text{mA}, I_B = -20\text{mA}^*$
	$V_{BE(sat)}$	-1.0	-1.0	V	$I_C = -100\text{mA}, I_B = -20\text{mA}^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-0.85	V	$I_C = -100\text{mA}, V_{CE} = -10\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100	300		$I_C = -1\text{mA}, V_{CE} = -10\text{V}$ $I_C = -50\text{mA}, V_{CE} = -10\text{V}^*$ $I_C = -100\text{mA}, V_{CE} = -10\text{V}^*$
Transition Frequency	$f_T$	75		MHz	$I_C = -50\text{mA}, V_{CE} = -10\text{V}$ $f = 100\text{MHz}$
Output Capacitance	$C_{obo}$		10	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$

\*Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤ 2%  
Spice parameter data is available upon request for this device

查询FM597供应商

捷多邦, 专业PCB打样工厂, 24小时加急出货

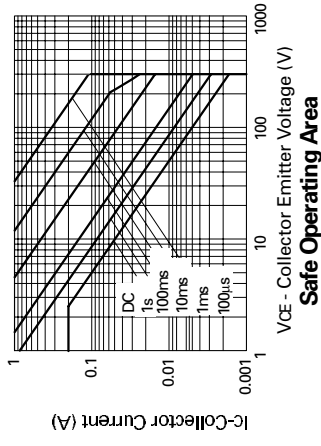
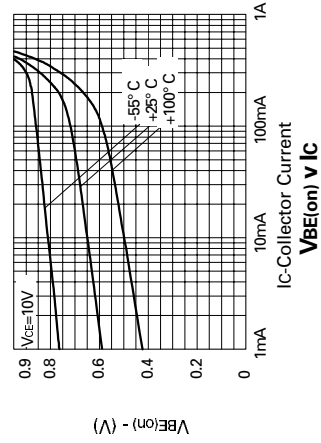
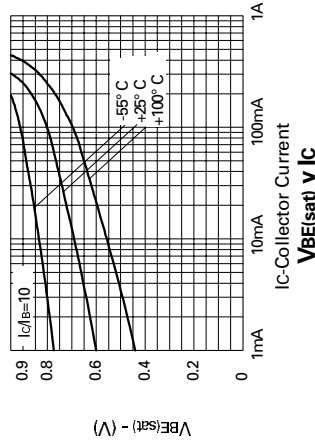
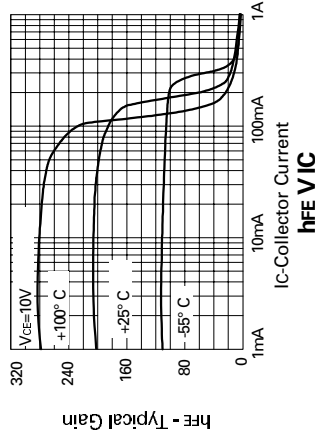
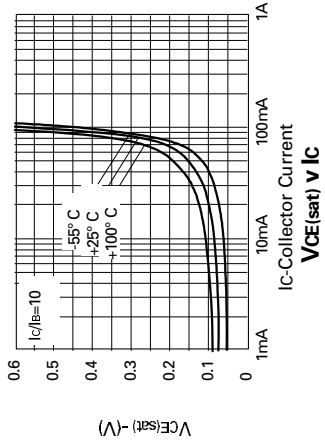
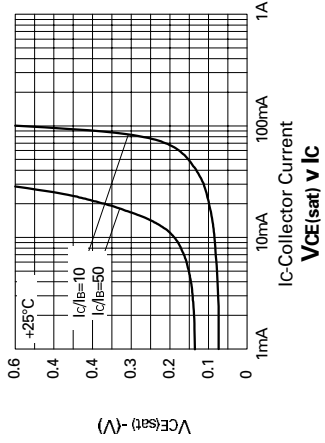
**SOT23 PNP SILICON PLANAR  
HIGH VOLTAGE TRANSISTOR**

ISSUE 3 - OCTOBER 1995

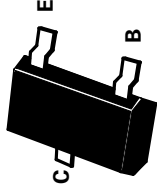
**FM5MT597**

**FM5MT597**

**TYPICAL CHARACTERISTICS**



COMPLEMENTARY TYPE FM5MT497  
PARTMARKING DETAIL - 597



**ABSOLUTE MAXIMUM RATINGS.**

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CB0}$	-300	V
Collector-Emitter Voltage	$V_{CE0}$	-300	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Peak Pulse Current	$I_{CM}$	-1	A
Continuous Collector Current	$I_C$	-0.2	A
Base Current	$I_B$	-200	mA
Power Dissipation at $T_{amb}=25^\circ\text{C}$	$P_{tot}$	500	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150	$^\circ\text{C}$

**ELECTRICAL CHARACTERISTICS (at  $T_{amb} = 25^\circ\text{C}$ ).**

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-300		V	$I_C=-100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300		V	$I_C=-10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E=-100\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$		-100	nA	$V_{CB}=-250\text{V}$
Emitter Cut-Off Current	$I_{EBO}$		-100	nA	$V_{EB}=-4\text{V}$
Collector-Emitter Cut-Off Current	$I_{CES}$		-100	nA	$V_{CES}=-250\text{V}$
Emitter Saturation Voltages	$V_{CE(sat)}$	-0.25	-0.25	V	$I_C=-50\text{mA}, I_B=-5\text{mA}$ $I_C=-100\text{mA}, I_B=-20\text{mA}^*$
	$V_{BE(sat)}$		-1.0	V	$I_C=-100\text{mA}, I_B=-20\text{mA}^*$
Base-Emitter Turn-on Voltage	$V_{BE(on)}$		-0.85	V	$I_C=-100\text{mA}, V_{CE}=-10\text{V}^*$
Static Forward Current Transfer Ratio	$h_{FE}$	100	300		$I_C=-1\text{mA}, V_{CE}=-10\text{V}$ $I_C=-50\text{mA}, V_{CE}=-10\text{V}^*$ $I_C=-100\text{mA}, V_{CE}=-10\text{V}^*$
Transition Frequency	$f_T$	75		MHz	$I_C=-50\text{mA}, V_{CE}=-10\text{V}$ $f=100\text{MHz}$
Output Capacitance	$C_{obo}$		10	pF	$V_{CB}=-10\text{V}, f=1\text{MHz}$

\*Measured under pulsed conditions. Pulse width=300µs. Duty cycle ≤ 2%  
Spice parameter data is available upon request for this device